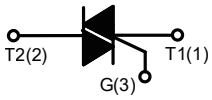
DESCRIPTION:

The Z0107MA SCR series with the parallel resistor between Gate and Cathode are especially recommended for use on straight hair, igniter, anion generator, etc.

TO-92



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	1	A
I_{TSM}	16	A
V_{TM}	≤1.5	V

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40 - 150	℃
Operating junction temperature range		T_j	-40 - 125	℃
Repetitive peak off-state voltage (T_j=25℃)		V_{DRM}	600/800	V
Repetitive peak reverse voltage (T_j=25℃)		V_{RRM}	600/800	V
Non repetitive surge peak off-state voltage		V_{DSM}	V_{DRM} + 100	V
Non repetitive peak reverse voltage		V_{RSM}	V_{RRM} + 100	V
RMS on-state current	TO-92 (T_C=50℃)	$I_{T(RMS)}$	1	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)		I_{TSM}	16	A
I^2t value for fusing (tp=10ms)		I^2t	1.28	A^2s
Critical rate of rise of on-state current (I_G=2×I_{GT})		dI/dt	20	A/μs
Peak gate current		I_{GM}	2	A
Average gate power dissipation		$P_{G(AV)}$	0.5	W
Peak gate power		P_{GM}	5	W

ELECTRICAL CHARACTERISTICS (T_j=25℃ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value		Unit
				T	D	
I_{GT}	V_D=12V R_L=33Ω	Ⅰ-Ⅱ-Ⅲ	MAX	5	5	mA
		Ⅳ		5	10	
V_{GT}		ALL	MAX	1.3		V
V_{GD}	V_D=V_{DRM} T_j=125℃ R_L=3.3KΩ	ALL	MIN	0.2		V
I_L	I_G=1.2I_{GT}	Ⅰ-Ⅲ	MAX	5	5	mA
		Ⅱ-Ⅳ		10	20	
I_H	I_T=200mA		MAX	5	7	mA
dV/dt	V_D=2/3V_{DRM} Gate Open T_j=125℃		MIN	15	20	V/μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	I_{TM}=1.4A tp=380μs	T_j=25℃	1.5	V
I_{DRM}	V_D=V_{DRM} V_R=V_{RRM}	T_j=25℃	5	μA
I_{RRM}		T_j=125℃	500	μA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-92	60	℃/W

FIG.1: Maximum power dissipation versus RMS on-state current

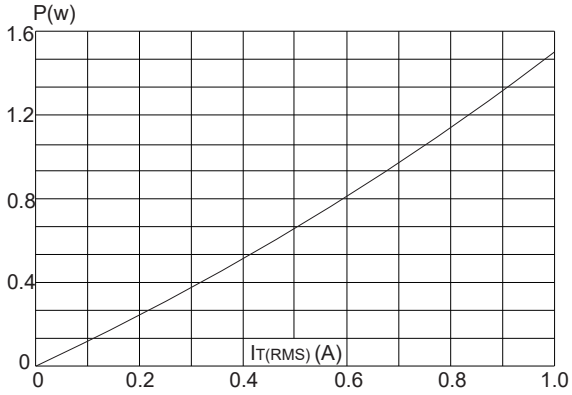


FIG.2: RMS on-state current versus case temperature

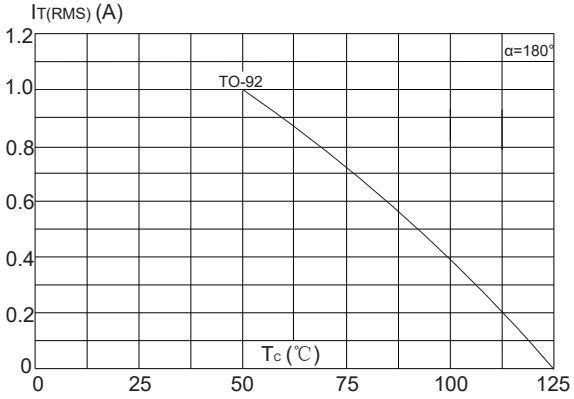


FIG.3: Surge peak on-state current versus number of cycles

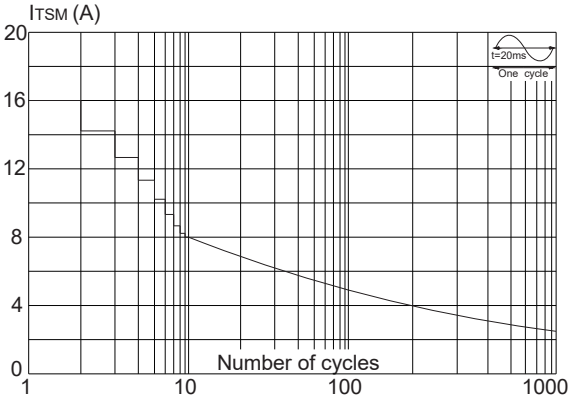


FIG.4: On-state characteristics (maximum values)

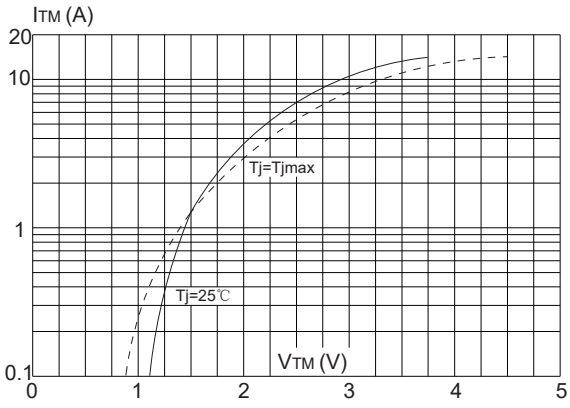


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms and corresponding value of I^2t (dI/dt < 20A/μs)

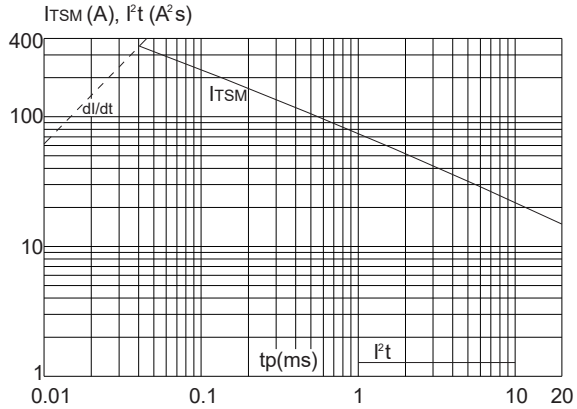


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature